NSN 5961-01-359-2009

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-359-2009 **Inclosure Material:** Metal **Overall Length:** 0.100 inches **Terminal Length:** 0.250 inches **Overall Height:** 0.050 inches **Overall Width:** 0.070 inches **Mounting Method: Terminal Features Provided:** Electrostatic sensitive **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 150.0 reverse breakdown voltage, instantaneous **Power Rating Per Characteristic:** 100.0 milliwatts small-signal input power, common-collector **Capacitance Rating In Picofarads:** 0.25 **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Terminal Type And Quantity:** 2 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:** No

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